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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner of Patents and Trademarks, Alexandria, VA.22313, on <u>June 25, 2004</u>. The applicant and/or attorney requests the date of deposit as the filing date. Depositor: Karen Cinq-Mars

PE (Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In se application of

Bruce B. Doris et al.

Group Art Unit: 2812

Serial No.10/605,672 :

Examiner: Stanetta D. Isaac

Filed: 10/16/2003

International Business Machines Corporation

2070 Route 52

Hopewell Junction, NY 12533

TITLE: High Pe

High Performance Strained CMOS Devices

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

The Commissioner is hereby authorized to charge the fees for this submission to Deposit Account No. 09-0458.

Respectfully submitted, Bruce B. Doris et al.

Joseph P. Abate, Attorne

Registration No. 30,238

Telephone No. 848-894-4633

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